



## STN1NC60

N-CHANNEL 600V - 12Ω - 0.3A - SOT-223

PowerMesh™ II MOSFET

TYPE	V <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>
STN1NC60	600 V	<15Ω	0.3 A

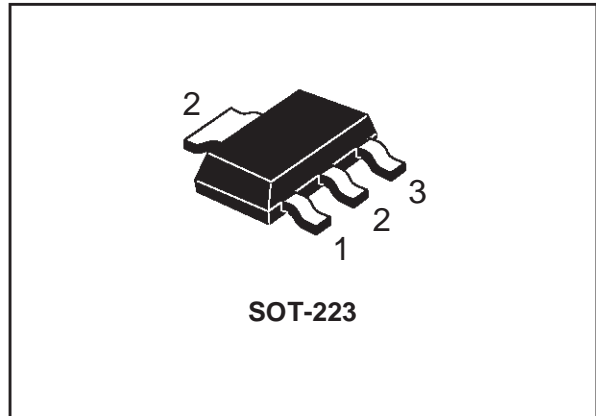
- TYPICAL R<sub>DS(on)</sub> = 12Ω
- EXTREMELY HIGH dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- NEW HIGH VOLTAGE BENCHMARK
- GATE CHARGE MINIMIZED

### DESCRIPTION

The PowerMESH™ II is the evolution of the first generation of MESH OVERLAY™. The layout refinements introduced greatly improve the Ron\*area figure of merit while keeping the device at the leading edge for what concerns switching speed, gate charge and ruggedness.

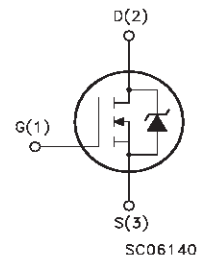
### APPLICATIONS

- AC ADAPTORS AND BATTERY CHARGERS
- SWITCH MODE POWER SUPPLIES (SMPS)



SOT-223

### INTERNAL SCHEMATIC DIAGRAM



### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V <sub>DS</sub>	Drain-source Voltage (V <sub>GS</sub> = 0)	600	V
V <sub>DGR</sub>	Drain-gate Voltage (R <sub>GS</sub> = 20 kΩ)	600	V
V <sub>GS</sub>	Gate- source Voltage	±30	V
I <sub>D</sub>	Drain Current (continuous) at T <sub>C</sub> = 25°C	0.3	A
I <sub>D</sub>	Drain Current (continuous) at T <sub>C</sub> = 100°C	0.18	A
I <sub>DM</sub> <sup>(1)</sup>	Drain Current (pulsed)	1.2	A
P <sub>TOT</sub>	Total Dissipation at T <sub>C</sub> = 25°C	2.5	W
	Derating Factor	0.02	W/°C
dv/dt	Peak Diode Recovery voltage slope	3	V/ns
T <sub>stg</sub>	Storage Temperature	-60 to 150	°C
T <sub>j</sub>	Max. Operating Junction Temperature	150	°C

(\*)Pulse width limited by safe operating area

(1)I<sub>SD</sub> ≤ 0.3A, di/dt ≤ 100A/μs, V<sub>DD</sub> ≤ V<sub>(BR)DSS</sub>, T<sub>j</sub> ≤ T<sub>JMAX</sub>

## STN1NC60

### THERMAL DATA

Rthj-pcb	Thermal Resistance Junction-PC Board	50	°C/W °C/W °C
Rthj-amb	Thermal Resistance Junction-ambient Max (Surface Mounted)	60	
T <sub>l</sub>	Maximum Lead Temperature For Soldering Purpose	260	

### AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I <sub>AR</sub>	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T <sub>j</sub> max)	0.3	A
E <sub>AS</sub>	Single Pulse Avalanche Energy (starting T <sub>j</sub> = 25 °C, I <sub>D</sub> = I <sub>AR</sub> , V <sub>DD</sub> = 50 V)	60	mJ

### ELECTRICAL CHARACTERISTICS (TCASE = 25 °C UNLESS OTHERWISE SPECIFIED)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source Breakdown Voltage	I <sub>D</sub> = 250 μA, V <sub>GS</sub> = 0	600			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current (V <sub>GS</sub> = 0)	V <sub>DS</sub> = Max Rating V <sub>DS</sub> = Max Rating, T <sub>C</sub> = 125 °C			1 50	μA μA
I <sub>GSS</sub>	Gate-body Leakage Current (V <sub>DS</sub> = 0)	V <sub>GS</sub> = ±30V			±100	nA

ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	2	3	4	V
R <sub>DS(on)</sub>	Static Drain-source On Resistance	V <sub>GS</sub> = 10V, I <sub>D</sub> = 0.5 A		12	15	Ω
I <sub>D(on)</sub>	On State Drain Current	V <sub>DS</sub> > I <sub>D(on)</sub> × R <sub>DS(on)max</sub> , V <sub>GS</sub> = 10V	1			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g <sub>fs</sub> (1)	Forward Transconductance	V <sub>DS</sub> > I <sub>D(on)</sub> × R <sub>DS(on)max</sub> , I <sub>D</sub> = 0.5A		0.87		S
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25V, f = 1 MHz, V <sub>GS</sub> = 0		108		pF
C <sub>oss</sub>	Output Capacitance			18		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			2.5		pF

**ELECTRICAL CHARACTERISTICS (CONTINUED)**

**SWITCHING ON**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ $t_r$	Turn-on Delay Time Rise Time	$V_{DD} = 300V, I_D = 0.5A$ $R_G = 4.7\Omega, V_{GS} = 10V$ (see test circuit, Figure 3)		7.2 8		ns ns
$Q_g$	Total Gate Charge	$V_{DD} = 480V, I_D = 1A,$ $V_{GS} = 10V$		7.3	10	nC
$Q_{gs}$	Gate-Source Charge			3.4		nC
$Q_{gd}$	Gate-Drain Charge			2.5		nC

**SWITCHING OFF**

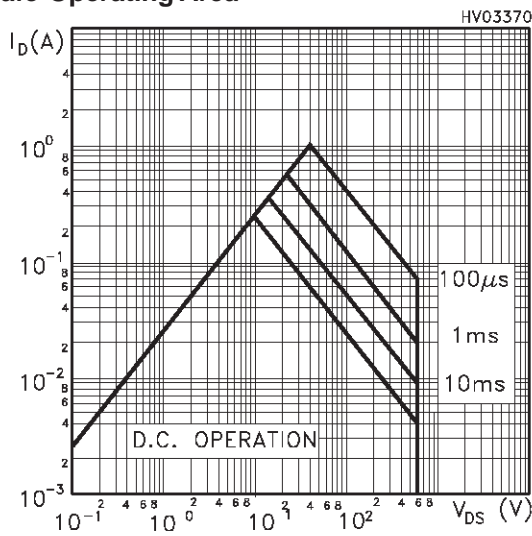
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$	Off-voltage Rise Time	$V_{DD} = 480V, I_D = 1A,$ $R_G = 4.7\Omega, V_{GS} = 10V$ (see test circuit, Figure 5)		33		ns
$t_f$	Fall Time			11		ns
$t_c$	Cross-over Time			43		ns

**SOURCE DRAIN DIODE**

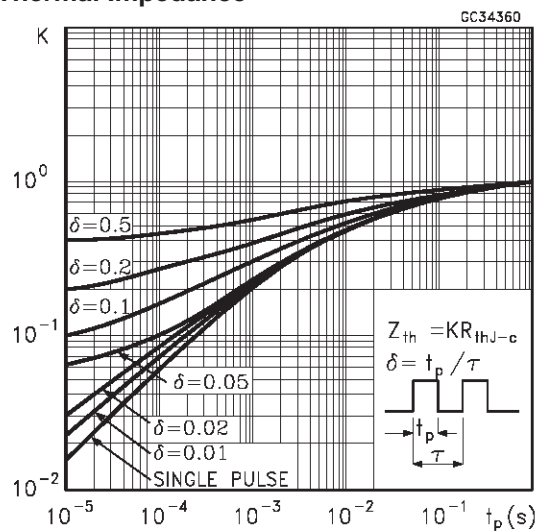
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain Current				0.3	A
$I_{SDM(2)}$	Source-drain Current (pulsed)				1.2	A
$V_{SD(1)}$	Forward On Voltage	$I_{SD} = 0.3 A, V_{GS} = 0$			1.6	V
$t_{rr}$	Reverse Recovery Time	$I_{SD} = 1A, di/dt = 100A/\mu s,$ $V_{DD} = 25V, T_j = 150^\circ C$ (see test circuit, Figure 5)		450		ns
$Q_{rr}$	Reverse Recovery Charge			720		$\mu C$
$I_{RRM}$	Reverse Recovery Current			3.2		A

Note: 1. Pulsed: Pulse duration = 300  $\mu s$ , duty cycle 1.5 %.  
2. Pulse width limited by safe operating area.

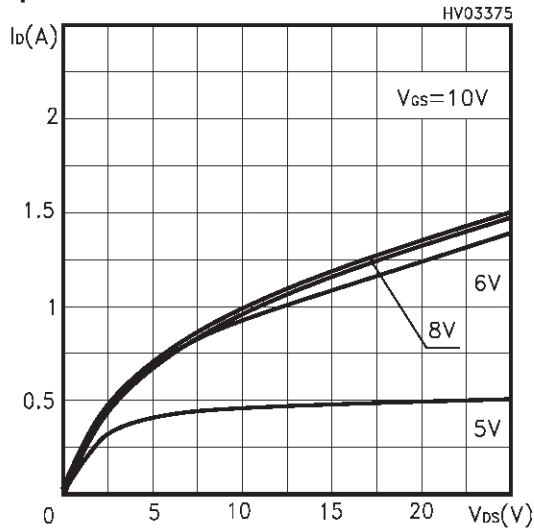
**Safe Operating Area**



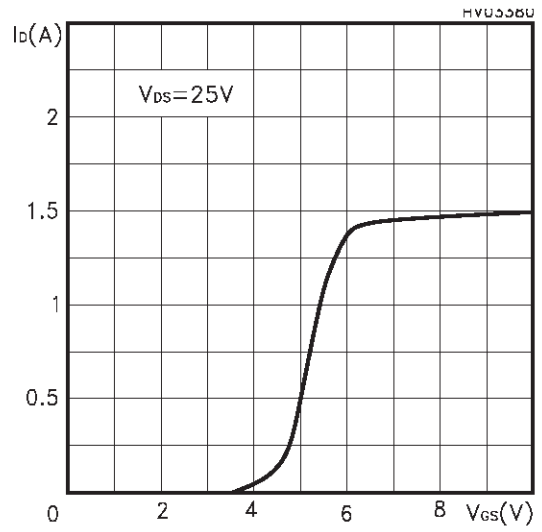
**Thermal Impedance**



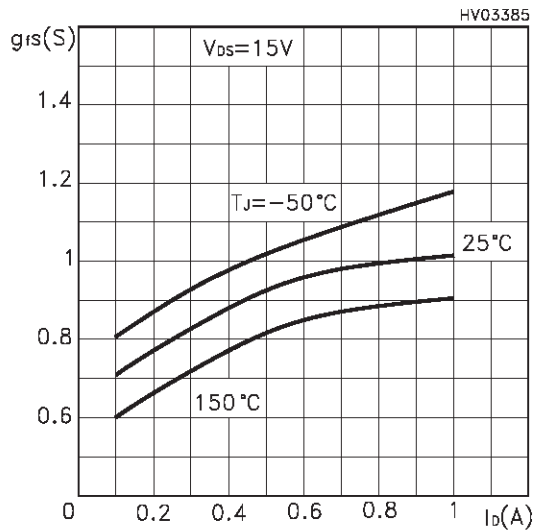
Output Characteristics



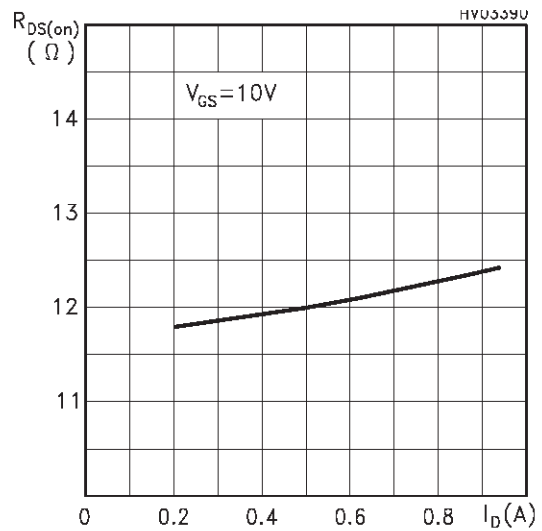
Transfer Characteristics



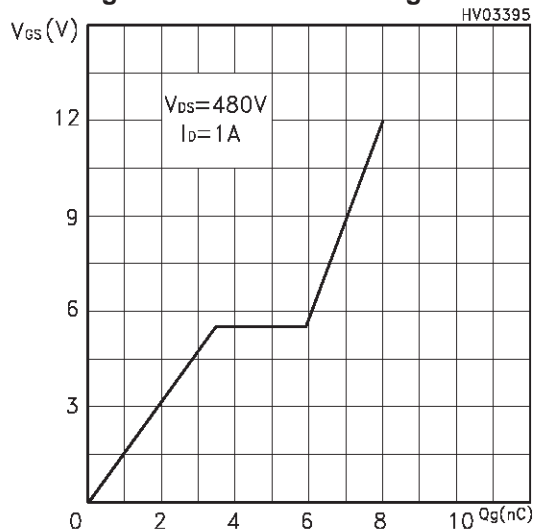
Transconductance



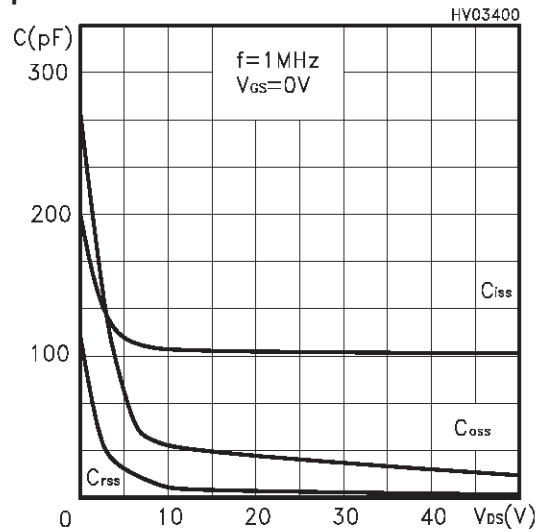
Static Drain-Source On Resistance



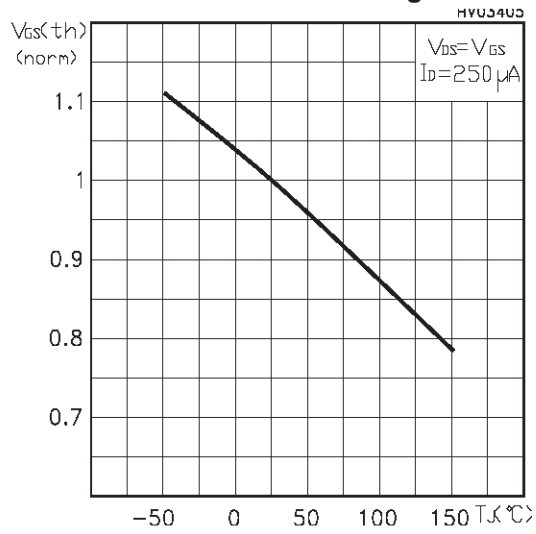
Gate Charge vs Gate-source Voltage



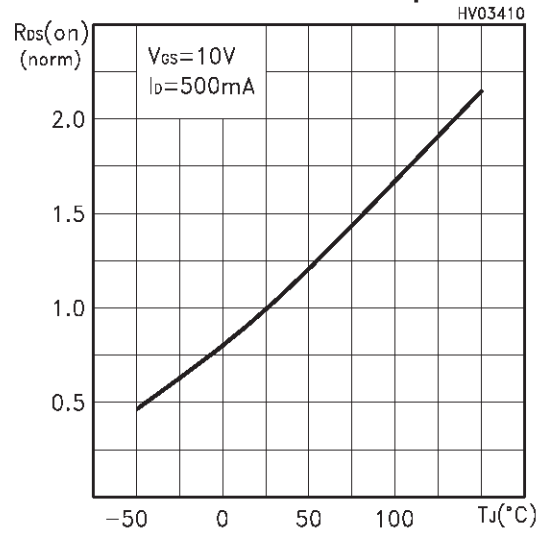
Capacitance Variations



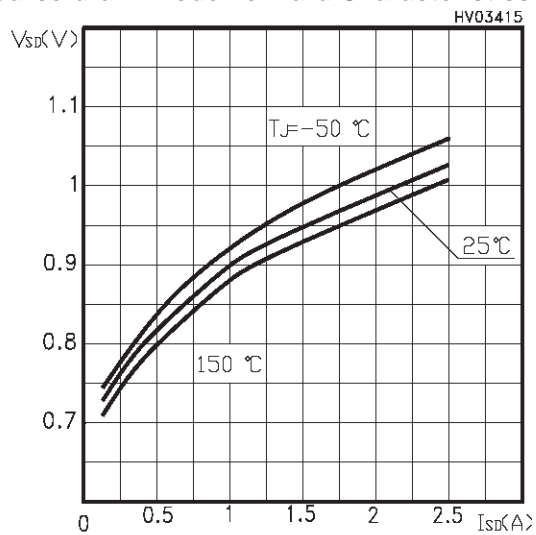
Normalized Gate Threshold Voltage vs Temp.



Normalized On Resistance vs Temperature



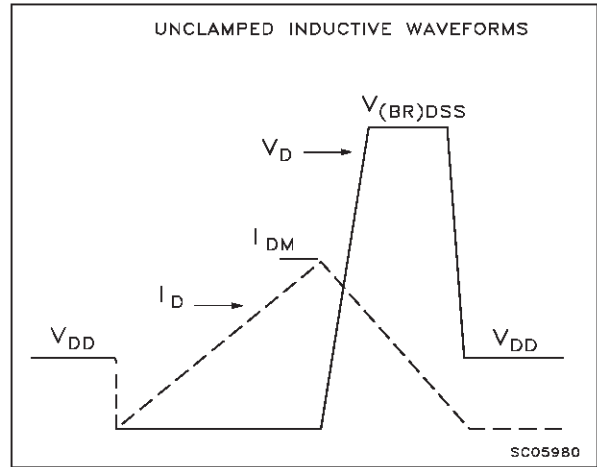
Source-drain Diode Forward Characteristics



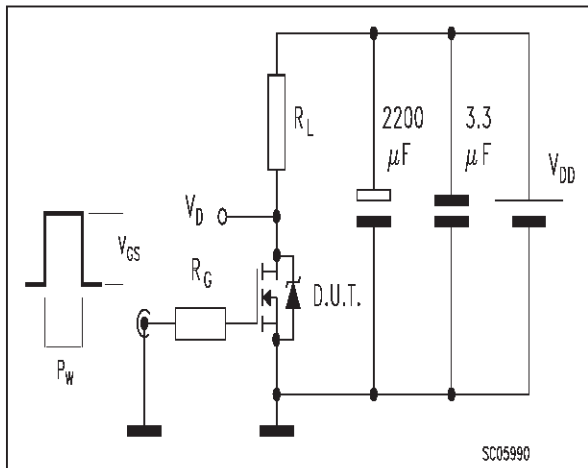
**Fig. 1: Unclamped Inductive Load Test Circuit**



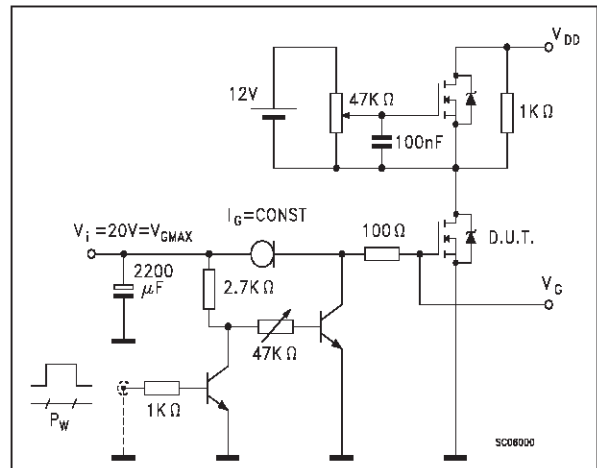
**Fig. 2: Unclamped Inductive Waveform**



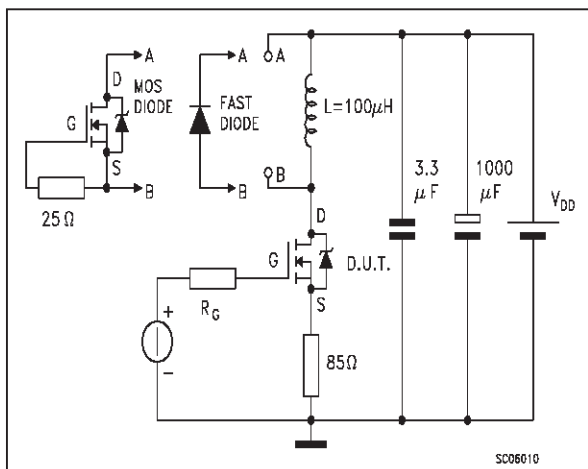
**Fig. 3: Switching Times Test Circuits For Resistive Load**



**Fig. 4: Gate Charge test Circuit**

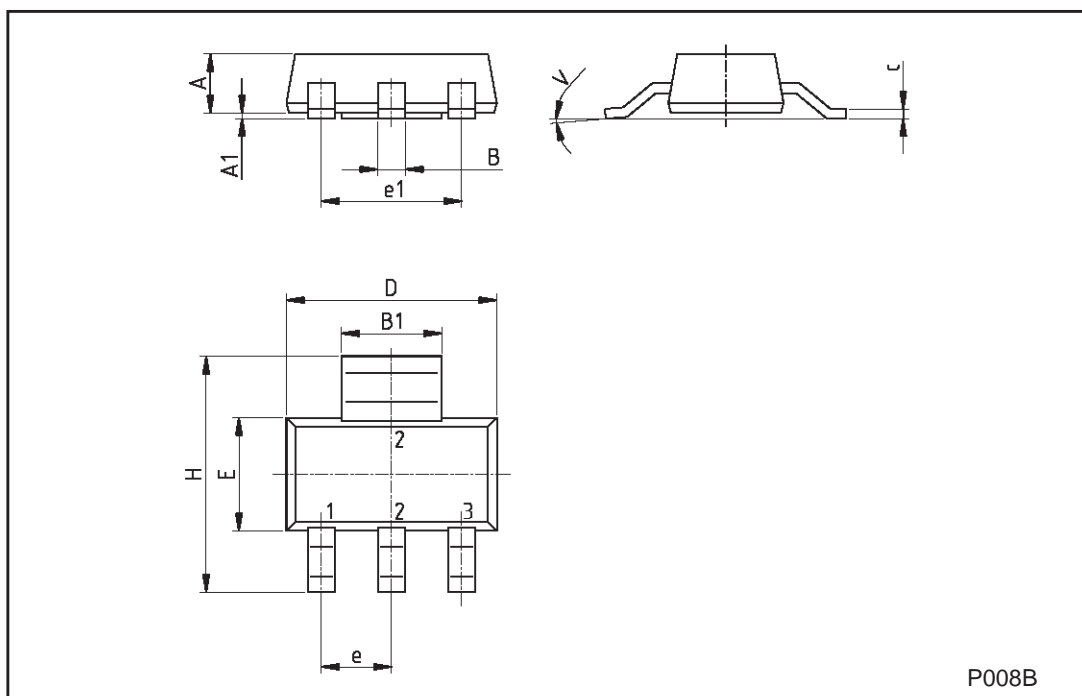


**Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times**



## SOT-223 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.80			0.071
B	0.60	0.70	0.80	0.024	0.027	0.031
B1	2.90	3.00	3.10	0.114	0.118	0.122
c	0.24	0.26	0.32	0.009	0.010	0.013
D	6.30	6.50	6.70	0.248	0.256	0.264
e		2.30			0.090	
e1		4.60			0.181	
E	3.30	3.50	3.70	0.130	0.138	0.146
H	6.70	7.00	7.30	0.264	0.276	0.287
V			10°			10°
A1		0.02				



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